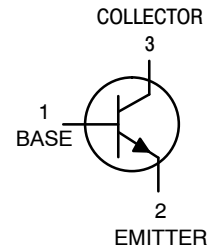


# General Purpose Transistors

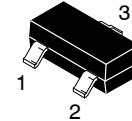
## NPN Silicon

### BC817-16L, SBC817-16L, BC817-25L, SBC817-25L, BC817-40L, SBC817-40L



#### Features

- S and NSV Prefixes for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant



SOT-23  
CASE 318  
STYLE 6

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	$V_{CEO}$	45	V
Collector – Base Voltage	$V_{CBO}$	50	V
Emitter – Base Voltage	$V_{EBO}$	5.0	V
Collector Current – Continuous	$I_C$	500	mAdc

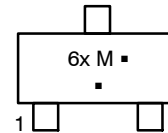
#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 = 1.0 x 0.75 x 0.062 in.
2. Alumina = 0.4 x 0.3 x 0.024 in 99.5% alumina.

#### MARKING DIAGRAM



- 6x = Device Code  
x = A, B, or C  
M = Date Code\*  
■ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

# BC817-16L, SBC817-16L, BC817-25L, SBC817-25L, BC817-40L, SBC817-40L

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Collector - Emitter Breakdown Voltage (I <sub>C</sub> = 10 mA)	V <sub>(BR)CEO</sub>	45	-	-	V
Collector - Emitter Breakdown Voltage (V <sub>EB</sub> = 0, I <sub>C</sub> = 10 μA)	V <sub>(BR)CES</sub>	50	-	-	V
Emitter - Base Breakdown Voltage (I <sub>E</sub> = 1.0 μA)	V <sub>(BR)EBO</sub>	5.0	-	-	V
Collector Cutoff Current (V <sub>CB</sub> = 20 V) (V <sub>CB</sub> = 20 V, T <sub>A</sub> = 150°C)	I <sub>CBO</sub>	-	-	100 5.0	nA μA

## ON CHARACTERISTICS

DC Current Gain (I <sub>C</sub> = 100 mA, V <sub>CE</sub> = 1.0 V)	BC817-16, SBC817-16 BC817-25, SBC817-25 BC817-40, SBC817-40	h <sub>FE</sub>	100	-	250	-
(I <sub>C</sub> = 500 mA, V <sub>CE</sub> = 1.0 V)			160	-	400	-
			250	-	600	-
			40	-	-	-
Collector - Emitter Saturation Voltage (I <sub>C</sub> = 500 mA, I <sub>B</sub> = 50 mA)	V <sub>CE(sat)</sub>	-	-	0.7	V	
Base - Emitter On Voltage (I <sub>C</sub> = 500 mA, V <sub>CE</sub> = 1.0 V)	V <sub>BE(on)</sub>	-	-	1.2	V	

## SMALL-SIGNAL CHARACTERISTICS

Current - Gain - Bandwidth Product (I <sub>C</sub> = 10 mA, V <sub>CE</sub> = 5.0 Vdc, f = 100 MHz)	f <sub>T</sub>	100	-	-	MHz
Output Capacitance (V <sub>CB</sub> = 10 V, f = 1.0 MHz)	C <sub>obo</sub>	-	10	-	pF

## SWITCHING CHARACTERISTICS

Delay Time (V <sub>CC</sub> = 3.0 Vdc, V <sub>BE</sub> = 0.5 V, I <sub>C</sub> = 10 mA)	t <sub>d</sub>	-	85	-	ns
Rise Time (V <sub>CC</sub> = 3.0 Vdc, V <sub>BE</sub> = 0.5 V, I <sub>C</sub> = 10 mA)	t <sub>r</sub>	-	30	-	ns
Storage Time (V <sub>CC</sub> = 3.0 Vdc, I <sub>C</sub> = 10 mA, I <sub>B1</sub> = 1 mA, I <sub>B2</sub> = 1 mA)	t <sub>s</sub>	-	1000	-	ns
Fall Time (V <sub>CC</sub> = 3.0 Vdc, I <sub>C</sub> = 10 mA, I <sub>B1</sub> = 1 mA, I <sub>B2</sub> = 1 mA)	t <sub>f</sub>	-	300	-	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## ORDERING INFORMATION

Device	Specific Marking	Package	Shipping†
BC817-16LT1G	6A	SOT-23 (Pb-Free)	3000 / Tape & Reel
NSVBC817-16LT1G			
BC817-16LT3G			10,000 / Tape & Reel
SBC817-16LT3G			
BC817-25LT1G	6B	SOT-23 (Pb-Free)	3000 / Tape & Reel
SBC817-25LT1G			
BC817-25LT3G			10,000 / Tape & Reel
SBC817-25LT3G			
BC817-40LT1G	6C	SOT-23 (Pb-Free)	3000 / Tape & Reel
SBC817-40LT1G			
BC817-40LT3G			10,000 / Tape & Reel
SBC817-40LT3G			

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS - BC817-16L, SBC817-16L

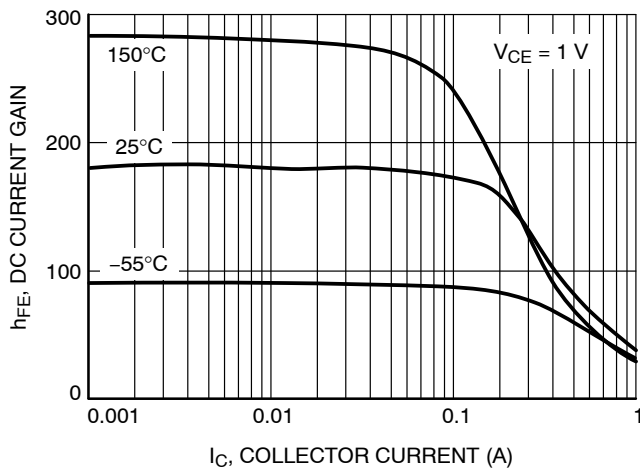


Figure 1. DC Current Gain vs. Collector Current

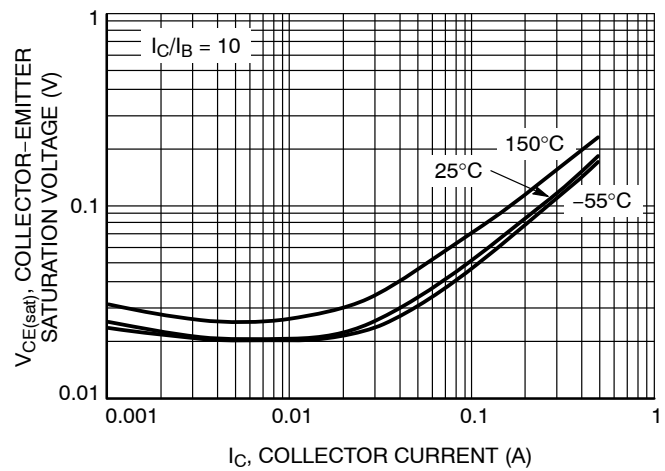


Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

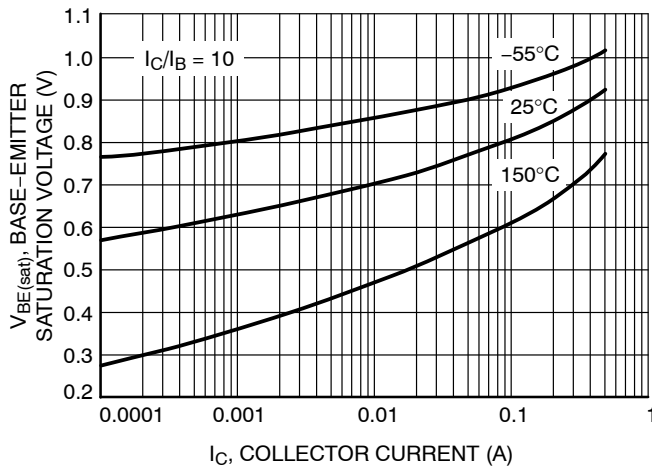


Figure 3. Base Emitter Saturation Voltage vs. Collector Current

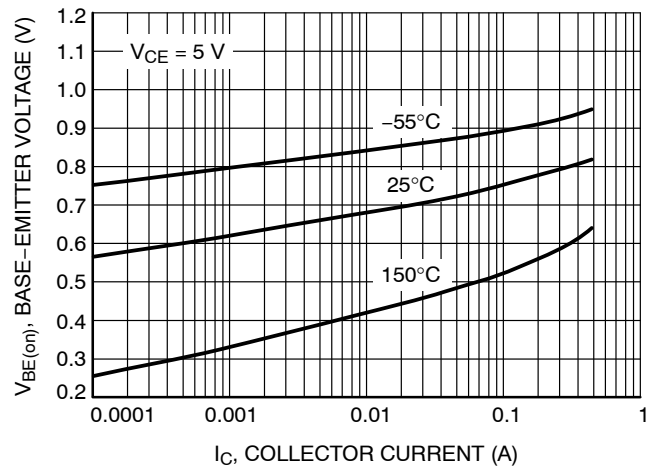


Figure 4. Base Emitter Voltage vs. Collector Current

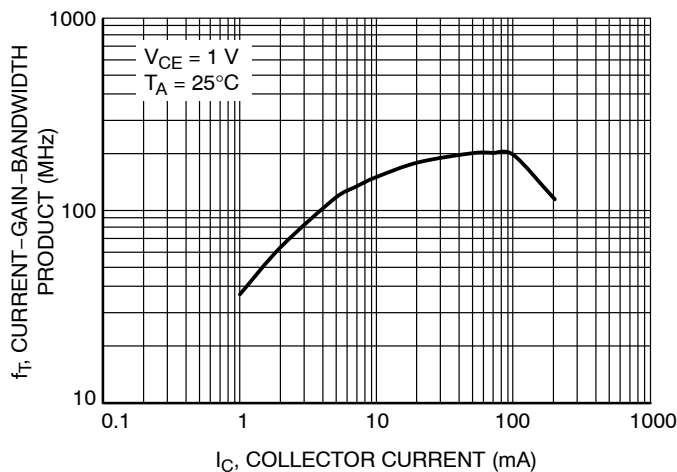


Figure 5. Current Gain Bandwidth Product vs. Collector Current

TYPICAL CHARACTERISTICS - BC817-16L, SBC817-16L

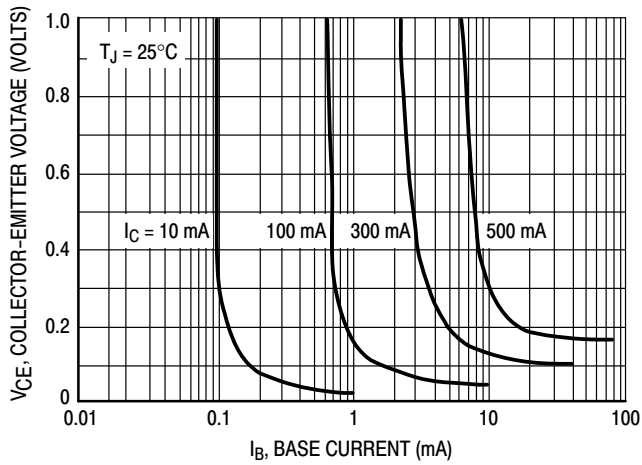


Figure 6. Saturation Region



Figure 7. Temperature Coefficients

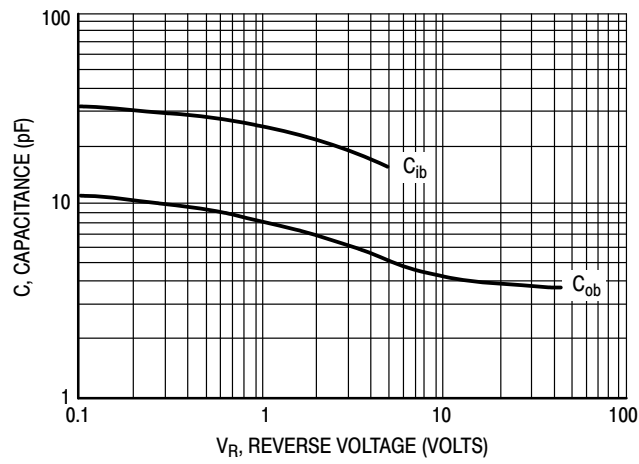


Figure 8. Capacitances

TYPICAL CHARACTERISTICS - BC817-25L, SBC817-25L

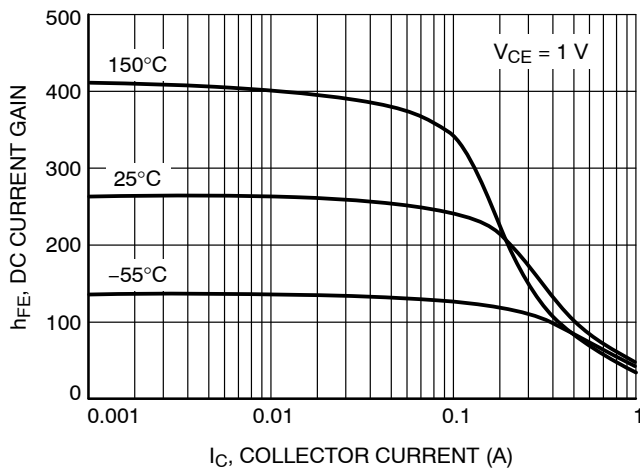


Figure 9. DC Current Gain vs. Collector Current

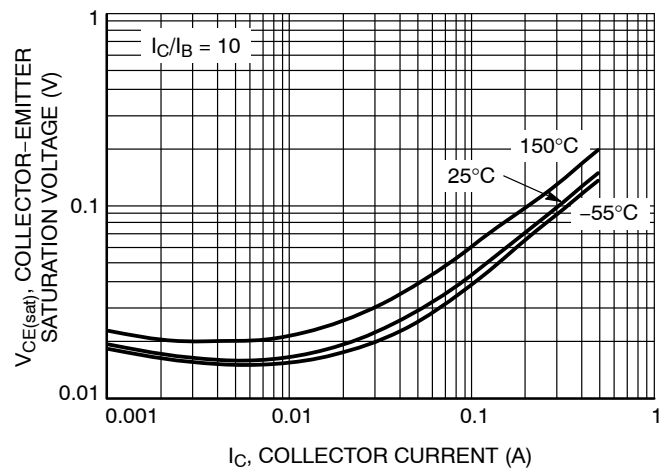


Figure 10. Collector Emitter Saturation Voltage vs. Collector Current



Figure 11. Base Emitter Saturation Voltage vs. Collector Current



Figure 12. Base Emitter Voltage vs. Collector Current

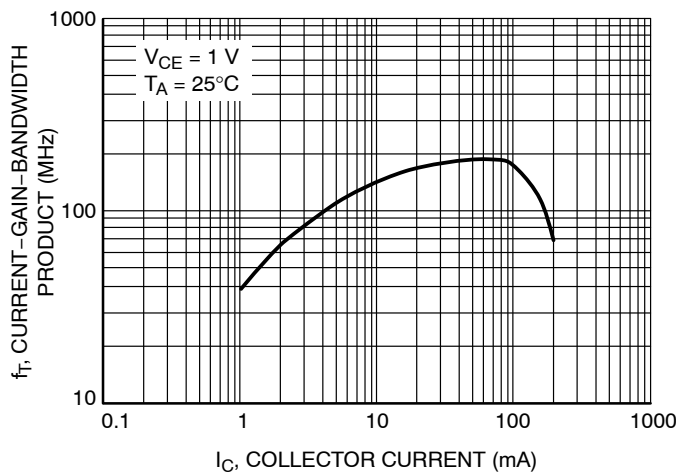


Figure 13. Current Gain Bandwidth Product vs. Collector Current

TYPICAL CHARACTERISTICS - BC817-25L, SBC81725L

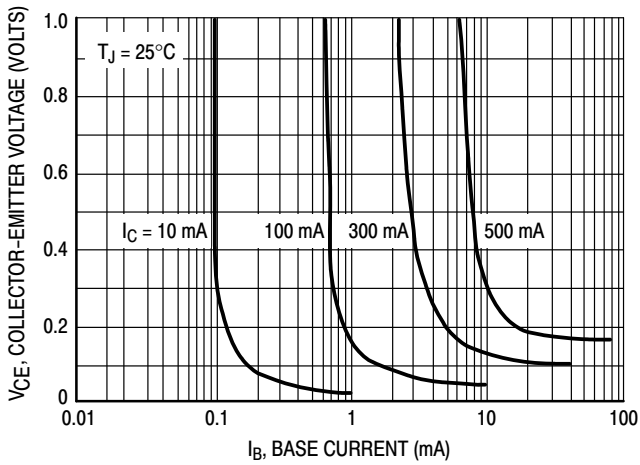


Figure 14. Saturation Region

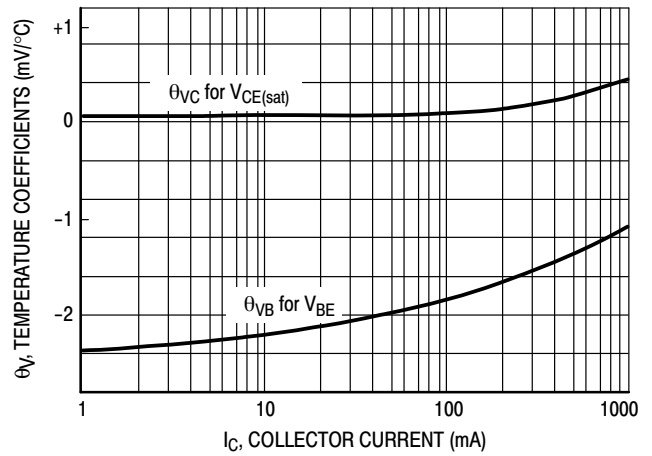


Figure 15. Temperature Coefficients



Figure 16. Capacitances

TYPICAL CHARACTERISTICS - BC817-40L, SBC817-40L



Figure 17. DC Current Gain vs. Collector Current

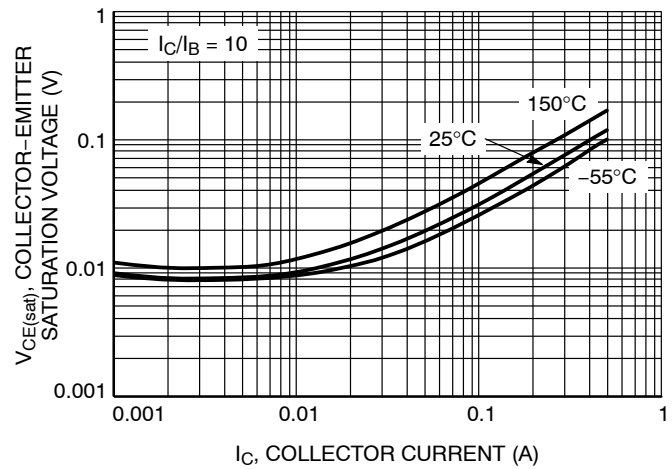


Figure 18. Collector Emitter Saturation Voltage vs. Collector Current



Figure 19. Base Emitter Saturation Voltage vs. Collector Current

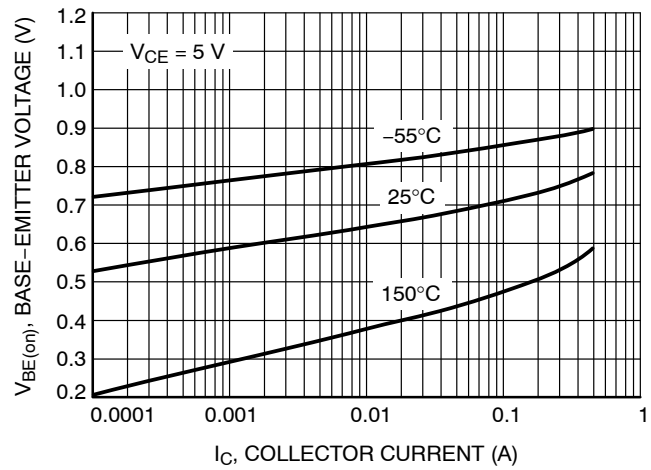


Figure 20. Base Emitter Voltage vs. Collector Current

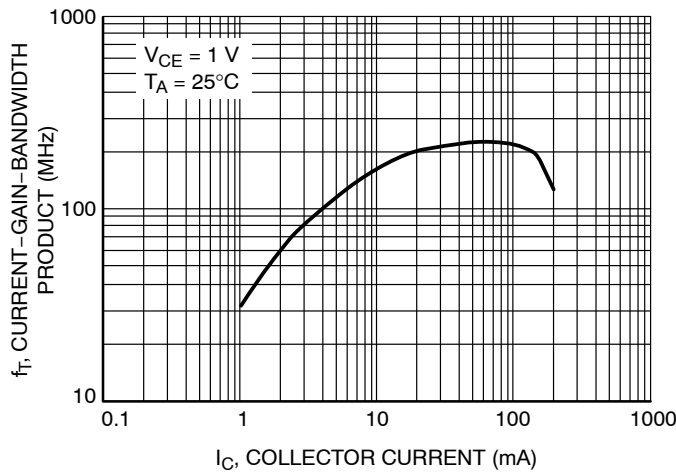


Figure 21. Current Gain Bandwidth Product vs. Collector Current

TYPICAL CHARACTERISTICS - BC817-40L, SBC817-40L

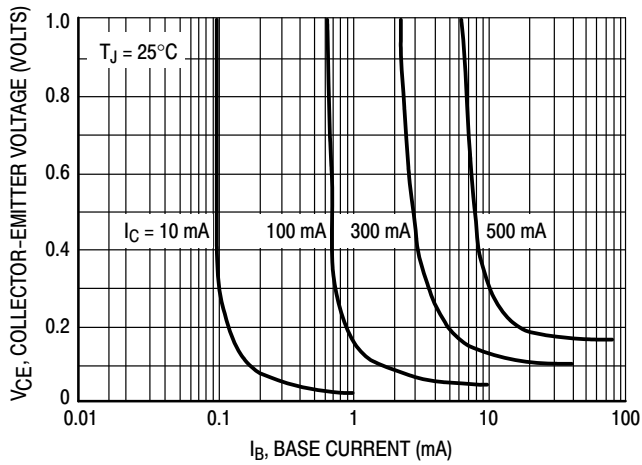


Figure 22. Saturation Region

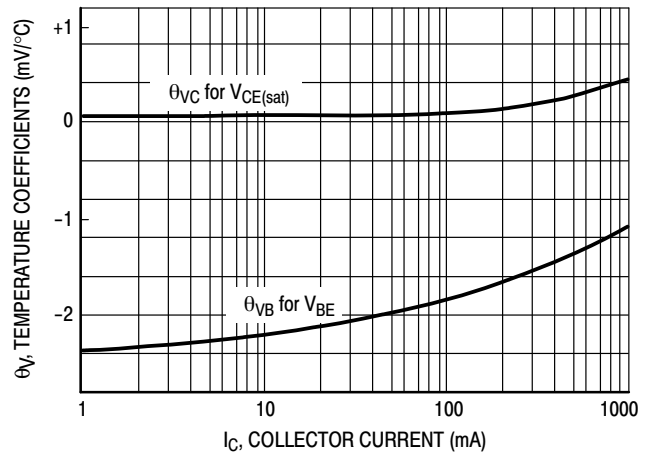


Figure 23. Temperature Coefficients



Figure 24. Capacitances



TYPICAL CHARACTERISTICS - BC817-16L, SBC817-16L, BC817-25L, SBC817-25L, BC817-40L, SBC817-40L

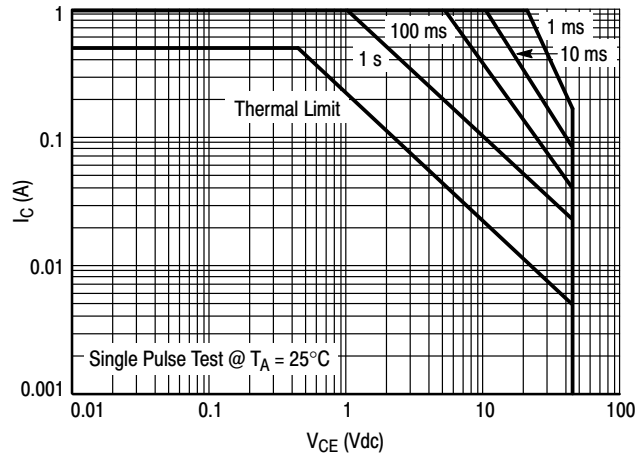


Figure 25. Safe Operating Area

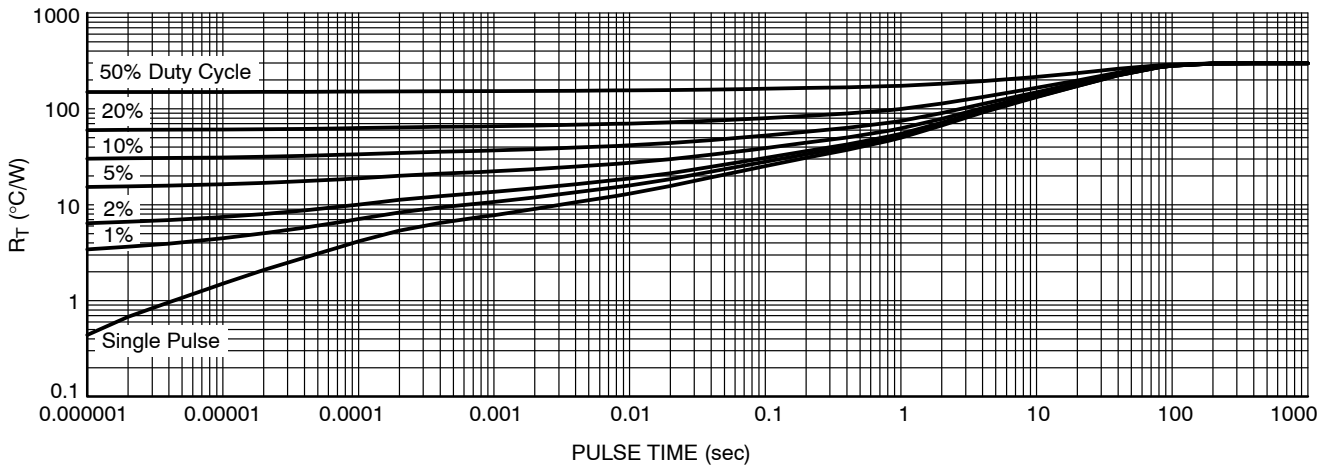


Figure 26. Thermal Response

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

ON Semiconductor®



**SOT-23 (TO-236)**  
CASE 318-08  
ISSUE AS

DATE 30 JAN 2018

SCALE 4:1



**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

**RECOMMENDED SOLDERING FOOTPRINT**



**GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

STYLE 1 THRU 5:  
CANCELLED

STYLE 6:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

STYLE 7:  
PIN 1. EMITTER  
2. BASE  
3. COLLECTOR

STYLE 8:  
PIN 1. ANODE  
2. NO CONNECTION  
3. CATHODE

STYLE 9:  
PIN 1. ANODE  
2. ANODE  
3. CATHODE

STYLE 10:  
PIN 1. DRAIN  
2. SOURCE  
3. GATE

STYLE 11:  
PIN 1. ANODE  
2. CATHODE  
3. CATHODE-ANODE

STYLE 12:  
PIN 1. CATHODE  
2. CATHODE  
3. ANODE

STYLE 13:  
PIN 1. SOURCE  
2. DRAIN  
3. GATE

STYLE 14:  
PIN 1. CATHODE  
2. GATE  
3. ANODE

STYLE 15:  
PIN 1. GATE  
2. CATHODE  
3. ANODE

STYLE 16:  
PIN 1. ANODE  
2. CATHODE  
3. CATHODE

STYLE 17:  
PIN 1. NO CONNECTION  
2. ANODE  
3. CATHODE

STYLE 18:  
PIN 1. NO CONNECTION  
2. CATHODE  
3. ANODE

STYLE 19:  
PIN 1. CATHODE  
2. ANODE  
3. CATHODE-ANODE

STYLE 20:  
PIN 1. CATHODE  
2. ANODE  
3. GATE

STYLE 21:  
PIN 1. GATE  
2. SOURCE  
3. DRAIN

STYLE 22:  
PIN 1. RETURN  
2. OUTPUT  
3. INPUT

STYLE 23:  
PIN 1. ANODE  
2. ANODE  
3. CATHODE

STYLE 24:  
PIN 1. GATE  
2. DRAIN  
3. SOURCE

STYLE 25:  
PIN 1. ANODE  
2. CATHODE  
3. GATE

STYLE 26:  
PIN 1. CATHODE  
2. ANODE  
3. NO CONNECTION

STYLE 27:  
PIN 1. CATHODE  
2. CATHODE  
3. CATHODE

STYLE 28:  
PIN 1. ANODE  
2. ANODE  
3. ANODE

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